L Number	Hits	Search Text	DB	Time stamp
1	45	(semiconductor near laser) and (active near (layer or region or	USPAT;	2004/05/25 10:31
		medium or film)) and (protection near (film or layer or	EPO; JPO;	
		region or medium)) and ridge and (refractive near (index or	DERWENT;	
		indice))	IBM_TDB	
4	2	(semiconductor near laser) and (active near (layer or region or	USPAT;	2004/05/25 10:31
		medium or film)) and (protection near2 dielectric near2 (film	EPO; JPO;	
		or layer or region or medium)) and ridge and (refractive near	DERWENT;	
_		(index or indice))	IBM_TDB	
3	14	((semiconductor near laser) and (active near (layer or region	USPAT;	2004/05/25 10:33
		or medium or film)) and (((dielectric or insulat\$5 or	EPO; JPO;	
		protect\$5) near (film or layer or region or medium)) same	DERWENT;	
		substrate same ridge same (refractive near (index or indice)))	IBM_TDB	
_	25	and width) and 257/\$	LICDATE	2004/05/25 10.00
2	25	((semiconductor near laser) and ((active near (layer or region	USPAT;	2004/05/25 10:39
		or medium or film)) AND (protection near (film or layer or	EPO; JPO;	
		region or medium)) SAME (SUBSTRATE)) and ridge and	DERWENT;	
_	-	(refractive near (index or indice))) and width	IBM_TDB	2004/05/25 10.04
5	1	((semiconductor near laser) and ((active near (layer or region	USPAT;	2004/05/25 10:34
į		or medium or film)) AND (dielectric near2 protection near	EPO; JPO;	
		(film or layer or region or medium)) SAME (SUBSTRATE))	DERWENT;	
	24	and ridge and (refractive near (index or indice))) and width	IBM_TDB	2004 (05 (25 10 20
- [34	(semiconductor near laser) and (active near (layer or region or	USPAT;	2004/05/25 10:30
		medium or film)) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice))	DERWENT;	
	26	((semigon duston moon loops) and (active moon (lover or region	IBM_TDB	2002 /05 /20 12.54
-	28	((semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/20 13:54
		or medium or film)) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice))) and width	DERWENT;	
	12	(semiconductor near laser) and ((active near (layer or region	IBM_TDB USPAT;	2002/05/20 10:37
-	12	or medium or film)) SAME (protection near (film or layer or	US-PGPUB;	2002/03/20 10.37
		region or medium)) SAME (SUBSTRATE)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
		(and the first of fides)	IBM_TDB	
_	21	(semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/20 15:02
	21	or medium or film)) AND (protection near (film or layer or	US-PGPUB;	2002, 00, 20 10.02
		region or medium)) SAME (SUBSTRATE)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
		(Alabara (Alabara))	IBM_TDB	
_	17	((semiconductor near laser) and ((active near (layer or region	USPAT;	2004/05/25 10:31
}		or medium or film)) AND (protection near (film or layer or	US-PGPUB;	
		region or medium)) SAME (SUBSTRATE)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))) and width	DERWENT;	
1		"	IBM_TDB	
-	10	((semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/20 14:24
		or medium or film)) SAME (protection near (film or layer or	US-PGPUB;	,,
		region or medium)) SAME (SUBSTRATE)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))) and width	DERWENT;	
		"	IBM_TDB	
-	12	(semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/20 16:36
		or medium or film)) AND (protection near (film or layer or	US-PGPUB;	
1		region or medium)) SAME (SUBSTRATE)) and (width same	EPO; JPO;	
		ridge) and (refractive near (index or indice))	DERWENT;	
			IBM_TDB	
-	11	((semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/21 08:26
1		or medium or film)) AND (protection near (film or layer or	US-PGPUB;	, ,
1		region or medium)) SAME (SUBSTRATE)) and (width same	EPO; JPO;	
1		ridge) and (refractive near (index or indice))) and 372/\$	DERWENT;	
		•	IBM_TDB	1

-	456	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/21 10:56
	- '	medium or film)) and ((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	
		near (film or layer or region or medium)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
1			IBM_TDB	
-	382	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/21 10:59
		medium or film)) and ((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	, ,
		near (film or layer or region or medium)) and ridge and	EPO; JPO;	
		(refractive near (index or indice)) AND substrate and width	DERWENT;	
		, , , , , , , , , , , , , , , , , , , ,	IBM_TDB	
_	0	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 13:14
		medium or film)) and (((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	, ,
		near (film or layer or region or medium)) same substrat) and	EPO; JPO;	
		ridge and (refractive near (index or indice)) and width	DERWENT;	
		8 (IBM_TDB	
_	284	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 13:18
		medium or film)) and (((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	2002, 00, 22 10:10
		near (film or layer or region or medium)) same substrate) and	EPO; JPO;	
		ridge and (refractive near (index or indice)) and width	DERWENT;	
		Truge and (remactive near (maex or maice)) and width	IBM_TDB	
	131	(comicanductor near locar) and (active near (layer or region or	USPAT;	2002/05/22 13:21
-	131	(semiconductor near laser) and (active near (layer or region or	US-PGPUB;	2002/05/22 15.21
		medium or film)) and (((dielectric or insulat\$5 or protect\$5)		
		near (film or layer or region or medium)) same substrate	EPO; JPO; DERWENT;	
		same ridge) and (refractive near (index or indice)) and width		
	20	(IBM_TDB	2002/05/22 14:21
-	29	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 14:31
		medium or film)) and (((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	
		near (film or layer or region or medium)) same substrate	EPO; JPO;	
		same ridge same (refractive near (index or indice))) and width	DERWENT;	
	20		IBM_TDB	0000 (05 (00 1 4 01
-	23	((semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 14:31
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge same (refractive near (index or indice)))	DERWENT;	
		and width) and 372/\$	IBM_TDB	2004/05/2540.24
-	6	((semiconductor near laser) and (active near (layer or region	USPAT;	2004/05/25 10:31
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge same (refractive near (index or indice)))	DERWENT;	
		and width) and 257/\$	IBM_TDB	
-	12	(semiconductor near device) and (active near (layer or region	USPAT;	2002/05/22 14:36
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	•
		substrate same ridge same (refractive near (index or indice)))	DERWENT;	
		and width	IBM_TDB	
-	30	(semiconductor near (device or laser)) and (active near (layer	USPAT;	2002/05/22 14:41
		or region or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge same (refractive near (index or indice)))	DERWENT;	
		and width	IBM_TDB	
-	344	(semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 10:54
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and ridge	EPO; JPO;	
		and refractive	DERWENT;	
			IBM_TDB	
-	114	(semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:23
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped)	DERWENT;	
			IBM_TDB	
		·		·

-	0	((semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:33
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped)) and	DERWENT;	
	400	(open\$5 near center) and (open\$5 near rear)	IBM_TDB	0000 /05 /01 10 00
-	108	((semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:38
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped)) and	DERWENT;	
	00	width	IBM_TDB USPAT;	2002/05/21 12:28
-	90	(((semiconductor with optical) and substrate and (active near	US-PGPUB;	2002/05/31 13:38
		(layer or film or region or medium)) and ((protect\$5 or	EPO; JPO;	
		insulat\$5) near (film or layer or region or medium)) and	DERWENT;	
		(ridge or groove) and refractive and (stripe near shaped)) and	IBM_TDB	
	27	width) and 372/\$ (semiconductor near laser) and (active near (layer or region or	USPAT;	2002/06/18 11:28
-	27	medium or film)) and (protection near (film or layer or	US-PGPUB;	2002/00/10 11.20
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
	1	indice)) and (open\$5)	DERWENT;	
	İ	make)) and (opendo)	IBM_TDB	
_	21	(semiconductor near laser) and (active near (layer or region or	USPAT;	2003/04/04 10:46
		medium or film)) and (protection near (film or layer or	US-PGPUB;	2000, 01, 01 10.10
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) and (open\$5) and (shap\$4)	DERWENT;	
			IBM_TDB	
-	3	("5029175" "5474954" "5805627").PN.	USPAT	2003/04/04 10:40
-	23	(semiconductor near laser) and (active near (layer or region or	USPAT;	2003/04/04 10:49
		medium or film)) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) and (open\$5) and (shap\$4) and width	DERWENT;	
			IBM_TDB	
-	57	(semiconductor near laser) and substrate and (active near	USPAT;	2003/04/04 11:06
		(layer or region or film or medium)) and (protection near	US-PGPUB;	
		(layer or region or film or medium)) and (ridge or stripe) and	EPO; JPO;	
		(refractive near (index or indice)) and width	DERWENT;	•
	18	(semiconductor near laser) and substrate and (active near	IBM_TDB USPAT;	2003/04/04 12:09
-	10	(layer or region or film or medium)) and (protection near	US-PGPUB;	2005/04/04 12.05
		(layer or region or film or medium)) and ((ridge or stripe)	EPO; JPO;	
		WITH (refractive near (index or indice))) and width	DERWENT;	
		Transfer of the control of the contr	IBM_TDB	
-	14	(semiconductor near laser) and substrate and (protection near	USPAT;	2003/04/04 12:40
		(layer or region or film or medium)) and ((ridge or stripe)	US-PGPUB;	. ,
		WITH (refractive near (index or indice)) WITH (active near	EPO; JPO;	
	1	(layer or region or film or medium))) and width	DERWENT;	
			IBM_TDB	
-	405	(semiconductor near laser) and (active near (layer or region or	USPAT;	2003/11/13 09:31
		medium or film)) and ((protect\$4 or dielectric) near (film or	US-PGPUB;	
	1	layer or region or medium)) and ridge and (refractive near	EPO; JPO;	
		(index or indice))	DERWENT;	
			IBM_TDB	2002 /11 /12 10 21
-	61	(semiconductor near laser) and (active near (layer or region or	USPAT;	2003/11/13 10:34
		medium or film)) and (protection near2 (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO; DERWENT;	
		indice))	IBM_TDB	
	5	(semiconductor near laser) and (active near (layer or region or	USPAT;	2004/05/25 10:31
1-		medium or film)) and (protection near2 dielectric near2 (film	US-PGPUB;	2007/03/23 10:31
		or layer or region or medium)) and ridge and (refractive near	EPO; JPO;	
	`	(index or indice))	DERWENT;	
		\	IBM_TDB	
	-	J		